# RICOH

## R3114x SERIES

#### 0.8% LOW VOLTAGE DETECTOR

NO.EA-160-120423

#### **OUTLINE**

The R3114x series are CMOS-based voltage detector ICs with high detector threshold accuracy and ultra-low supply current, which can be operated at an extremely low voltage and is used for system reset as an example.

Each of these ICs consists of a voltage reference unit, a comparator, resistors for detector threshold setting, an output driver and a hysteresis circuit. The detector threshold is fixed with high accuracy internally and does not require any adjustment.

Two output types, Nch open drain type and CMOS type are available.

The R3114x series are operable at a lower voltage than that of the R3111x series, and can be driven by a single battery.

Three types of packages, SOT-23-5, SC-82AB, and DFN(PLP)1010-4 are available.

#### **FEATURES**

Supply Current	Typ. 0.35μA (-Vdet=1.5V, Vdd=-Vdet+1V)
Operating Voltage Range	
Detector Threshold Range	
	(For other voltages, please refer to MARK INFORMATIONS.)
Detector Threshold Accuracy	$\pm 0.8\%$ (-VDET $\geq 1.5$ V)
• Temperature-Drift Coefficient of Detector Thresho	ldTyp. ±30ppm/°C
Output Types	Nch Open Drain "L" and CMOS
Packages	DFN(PLP)1010-4, SC-82AB, SOT-23-5

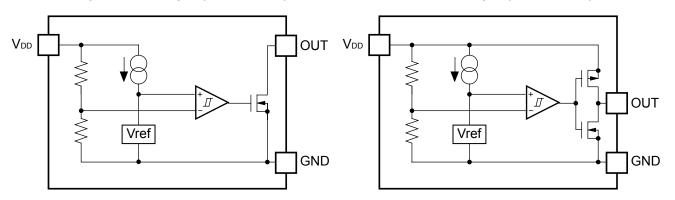
#### **APPLICATIONS**

- CPU and Logic Circuit Reset
- Battery Checker
- Window Comparator
- · Wave Shaping Circuit
- · Battery Back-up Circuit
- · Power Failure Detector

### **BLOCK DIAGRAMS**

#### Nch Open Drain Output (R3114xxx1A)

#### CMOS Output (R3114xxx1C)



#### **SELECTION GUIDE**

The package type, the detector threshold, the output type and the taping type for the ICs can be selected at the users' request.

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R3114Kxx1*-TR	DFN(PLP)1010-4	10,000 pcs	Yes	Yes
R3114Qxx1*-TR-FE	SC-82AB	3,000 pcs	Yes	Yes
R3114Nxx1*-TR-FE	SOT-23-5	3,000 pcs	Yes	Yes

xx: The detector threshold can be designated in the range from 0.7V(07) to 5.0V(50) in 0.1V steps. (For other voltages, please refer to MARK INFORMATIONS.)

- \* : Designation of Output Type(A) Nch Open Drain

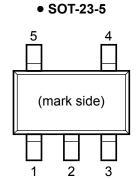
  - (C) CMOS

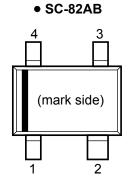
### **PIN CONFIGURATIONS**

• DFN(PLP)1010-4\*

Top View
4 3

Bottom View
3 4





### **PIN DESCRIPTIONS**

### • DFN(PLP)1010-4\*

Pin No.	Symbol	Description
1	OUT	Output Pin ("L" at detection)
2	NC	No Connection
3	GND	Ground Pin
4	V <sub>DD</sub>	Input Pin

\*) Tab is GND level. (They are connected to the reverse side of this IC.)

The tab is better to be connected to the GND, but leaving it open is also acceptable.

#### • SOT-23-5

Pin No.	Symbol	Description
1	OUT	Output Pin ("L" at detection)
2	$V_{DD}$	Input Pin
3	GND	Ground Pin
4	NC	No Connection
5	NC	No Connection

#### • SC-82AB

Pin No.	Symbol	Description
1	OUT	Output Pin ("L" at detection)
2	$V_{DD}$	Input Pin
3	NC	No Connection
4	GND	Ground Pin

### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Item	Rating	Unit
V <sub>DD</sub>	Supply Voltage	7.0	V
Vоит	Output Voltage (Nch Open Drain Output)	Vss-0.3 to 7.0	V
<b>V</b> 001	Output Voltage (CMOS Output)	Vss-0.3 to VDD+0.3	V
Іоит	Output Current	20	mA
	Power Dissipation (SOT-23-5)*	420	
PD	Power Dissipation (SC-82AB)*	380	mW
	Power Dissipation (DFN(PLP)1010-4)*	400	
Topt	Operating Temperature Range	-40 to 85	°C
Tstg	Storage Temperature Range	–55 to 125	°C

<sup>\*)</sup> For Power Dissipation, please refer to PACKAGE INFORMATION.

#### **ABSOLUTE MAXIMUM RATINGS**

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause the permanent damages and may degrade the life time and safety for both device and system using the device in the field.

The functional operation at or over these absolute maximum ratings is not assured.

#### RECOMMENDED OPERATING CONDITIONS (ELECTRICAL CHARACTERISTICS)

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

### **ELECTRICAL CHARACTERISTICS**

• R3114xxx1A/C values indicate −40°C ≤ Topt ≤ 85°C, unless otherwise noted. Topt=25°C

Symbol	Item		Cond	itions		Min.	Тур.	Max.	Unit
		Topt=25	5°C	1.5V < -	$V_{\text{DET}} \leq 5.0 V$	-V <sub>DET</sub> × 0.992		-V <sub>DET</sub> ×1.008	V
-V <sub>DET</sub>	Detector Threshold			0.7V ≤ -	$0.7V \le -V_{DET} \le 1.5V$			+12	mV
-VDET	Detector Threshold	-40°C	≤ Topt ≤ 85°C	1.5V < -	$V_{\text{DET}} \leq 5.0 V$	-V <sub>DET</sub> × 0.985		-V <sub>DET</sub> × 1.015	V
				0.7V ≤ -	$V_{\text{DET}} \leq 1.5 V$	-22.5		+22.5	mV
V <sub>HYS</sub>	Detector Threshold Hysteresis					-V <sub>DET</sub> × 0.04		$\begin{array}{c} \text{-V}_{\text{DET}} \\ \times \ 0.07 \end{array}$	<b>V</b>
				0.7V ≤ -	V <sub>DET</sub> < 1.6V			1.40	
		Von- V	DET -0.1V	1.6V ≤ -	V <sub>DET</sub> < 3.1V			1.50	
	<b>V</b> DD— <b>- V</b>	DET - <b>U. I V</b>	3.1V ≤ -	V <sub>DET</sub> < 4.1V			1.60		
lee	Iss Supply Current			4.1V ≤ -	$V_{\text{DET}} \leq 5.0 V$			1.70	μΑ
155	Supply Suitent			0.7V ≤ -	V <sub>DET</sub> < 1.6V			1.20	μΛ
		V <sub>DD</sub> =-V <sub>DET</sub> +0.1V		1.6V ≤ -	1.6V ≤ -V <sub>DET</sub> < 3.1V			1.20	
				$3.1V \le -V_{DET} < 4.1V$				1.30	
				$4.1V \leq \text{-V}_{\text{DET}} \leq 5.0V$				1.40	
V <sub>DDH</sub>	Maximum Operating Voltage							6	V
V <sub>DDL</sub>	Minimum Operating	Topt=25	5°C					0.50	V
V DDL	Voltage*1	-40°C	$\leq$ Topt $\leq$ 85°C					0.55	V
			VDD=0.55V, V	os=0.05V		7			μΑ
			0.7V ≤ -V <sub>DET</sub> < 1.1V		V <sub>DD</sub> =0.6V V <sub>DS</sub> =0.5V	0.02			
		Nch	111V/<-\/pr=<16V/		V <sub>DD</sub> =1.0V V <sub>DS</sub> =0.5V	0.40			- mA
Іоит	Output Current (Driver Output Pin)		1.6V ≤ -V <sub>DET</sub> < 3.1V		V <sub>DD</sub> =1.5V V <sub>DS</sub> =0.5V	1.00			ША
	(Briver Gutput Firi)		3.1V ≤ -VDET	$3.1V \le -V_{DET} \le 5.0V$		2.40			
		Pch*2	0.7V ≤ -VDET	$V_{DS} = 0.5V$ $V_{DS} = 0.5V$ $V_{DD} = 4.5V$ $V_{DS} = -2.1$		0.65			mΛ
		PCN	4  IIV < -VDET < 5  IIV		V <sub>DD</sub> =6.0V V <sub>DS</sub> =-2.1V	0.90			mA
ILEAK	Nch Driver Leakage Current*3	V <sub>DD</sub> =6.0	V <sub>DD</sub> =6.0V, V <sub>DS</sub> =7.0V					80	nA
$\Delta$ -V <sub>DET</sub> /	Detector Threshold						±30		ppm
$\DeltaTopt$	Temperature Coefficient								/°C
<b>t</b> PLH	Output Delay Time	V <sub>DD</sub> =0.	55V to -V <sub>DET</sub> +2	.0V or 6.0	V		40		μS

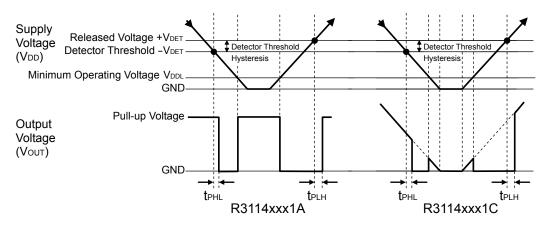
All of unit are tested and specified under load conditions such that Topt=25°C except for Detector Threshold Temperature Coefficient.

<sup>\*1:</sup> Minimum operating voltage means the value of input voltage when output voltage maintains 0.1V or less. (In case of Nch Open Drain Output type, the output pin is pulled up with a resistance of  $470k\Omega$  to 5.0V)

<sup>\*2:</sup> In case of CMOS type

<sup>\*3:</sup> In case of Nch Open Drain type

#### **TIMING CHART**



#### **DEFINITION OF OUTPUT DELAY TIME**

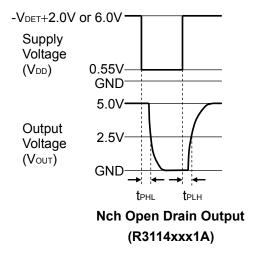
Output Delay Time (tplh) is defined as follows:

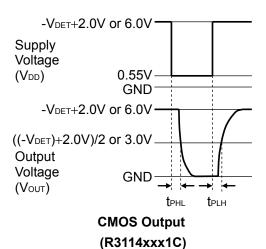
1. In the case of Nch Open Drain Output:

Under the condition of the output pin (OUT) is pulled up through a resistor of  $470k\Omega$  to 5V, the time interval between the rising edge of V<sub>DD</sub> pulse from 0.55V to (-V<sub>DET</sub>)+2.0V or the time interval of 6.0V pulse voltage is supplied, the becoming of the output voltage to 2.5V.

2. In the case of CMOS Output:

The time interval between the rising edge of  $V_{DD}$  pulse from 0.55V to  $(-V_{DET})+2.0V$  or the time interval of 6.0V pulse voltage is supplied, the becoming of the output voltage to  $((-V_{DET})+2.0V)/2$  or 3.0V.





### **ELECTRICAL CHARACTERISTICS BY DETECTOR THRESHOLD**

#### • R3114x071A/C to R3114x501A/C

Bold values are checked and guaranteed by design engineering at −40°C ≤ Topt ≤ 85°C, unless otherwise noted.

Topt=25°C

	Detector Threshold1		Detector Threshold Supply Current1 Supply Current					Current2	Max. Op.													
Part					Hyste	eresis															Voltage	Voltage
Number	<b>-V</b> DE	T1 [V]	-VDE	г2 <b>[V]</b>	VHY	s [V]	Iss1	Issı [µA]		Iss₂ [μA]		VDDL [V]										
	Min.	Max.	Min.	Max.	Min.	Max.	Cond.	Max.	Cond.	Max.	Max.	Max.										
R3114x071A/C	0.6880	0.7120	0.6775	0.7225	0.028	0.049																
R3114x081A/C	0.7880	0.8120	0.7775	0.8225	0.032	0.056	]															
R3114x091A/C	0.8880	0.9120	0.8775	0.9225	0.036	0.063																
R3114x101A/C	0.9880	1.0120	0.9775	1.0225	0.040	0.070																
R3114x111A/C	1.0880	1.1120	1.0775	1.1225	0.044	0.077		1.400														
R3114x121A/C	1.1880	1.2120	1.1775	1.2225	0.048	0.084																
R3114x131A/C	1.2880	1.3120	1.2775	1.3225	0.052	0.091																
R3114x141A/C	1.3880	1.4120	1.3775	1.4225	0.056	0.098																
R3114x151A/C	1.4880	1.5120	1.4775	1.5225	0.060	0.105																
R3114x161A/C	1.5872	1.6128	1.5760	1.6240	0.064	0.112	ļ															
R3114x171A/C	1.6864	1.7136	1.6745	1.7255	0.068	0.119																
R3114x181A/C	1.7856	1.8144	1.7730	1.8270	0.072	0.126				1.200												
R3114x191A/C	1.8848	1.9152	1.8715	1.9285	0.076	0.133				11200												
R3114x201A/C	1.9840	2.0160	1.9700	2.0300	0.080	0.140																
R3114x211A/C	2.0832	2.1168	2.0685	2.1315	0.084	0.147																
R3114x221A/C	2.1824	2.2176	2.1670	2.2330	0.088	0.154																
R3114x231A/C	2.2816	2.3184	2.2655	2.3345	0.092	0.161		1.500														
R3114x241A/C	2.3808	2.4192	2.3640	2.4360	0.096	0.168																
R3114x251A/C	2.4800	2.5200	2.4625	2.5375	0.100	0.175						0.50										
R3114x261A/C	2.5792	2.6208	2.5610	2.6390	0.104	0.182						0.50										
R3114x271A/C	2.6784	2.7216	2.6595	2.7405	0.108	0.189	V <sub>DD</sub> =		V <sub>DD</sub> =													
R3114x281A/C	2.7776	2.8224	2.7580	2.8420	0.112	0.196	-VDD=		-VDET +1.0V		6	0.55										
R3114x291A/C	2.8768	2.9232	2.8565	2.9435	0.116	0.203	-0.1V					0.00										
R3114x301A/C	2.9760	3.0240	2.9550	3.0450	0.120	0.210	0.10															
R3114x311A/C	3.0752	3.1248	3.0535	3.1465	0.124	0.217						*Note1										
R3114x321A/C	3.1744	3.2256	3.1520	3.2480	0.128	0.224																
R3114x331A/C	3.2736	3.3264	3.2505	3.3495	0.132	0.231																
R3114x341A/C	3.3728	3.4272	3.3490	3.4510	0.136	0.238																
R3114x351A/C	3.4720	3.5280	3.4475	3.5525	0.140	0.245		1.600		1.300												
R3114x361A/C	3.5712	3.6288	3.5460	3.6540	0.144	0.252		1.000		1.500												
R3114x371A/C	3.6704	3.7296	3.6445	3.7555	0.148	0.259	ļ															
R3114x381A/C	3.7696	3.8304	3.7430	3.8570	0.152	0.266	ļ															
R3114x391A/C	3.8688	3.9312	3.8415	3.9585	0.156	0.273																
R3114x401A/C	3.9680	4.0320	3.9400	4.0600	0.160	0.280					]											
R3114x411A/C	4.0672	4.1328	4.0385	4.1615	0.164	0.287				<u>-</u>												
R3114x421A/C	4.1664	4.2336	4.1370	4.2630	0.168	0.294																
R3114x431A/C	4.2656	4.3344	4.2355	4.3645	0.172	0.301																
R3114x441A/C	4.3648	4.4352	4.3340	4.4660	0.176	0.308																
R3114x451A/C	4.4640	4.5360	4.4325	4.5675	0.180	0.315		1.700		1.400												
R3114x461A/C	4.5632	4.6368	4.5310	4.6690	0.184	0.322	Į	1.700		1.400												
R3114x471A/C	4.6624	4.7376	4.6295	4.7705	0.188	0.329	Į															
R3114x481A/C	4.7616	4.8384	4.7280	4.8720	0.192	0.336	Į															
R3114x491A/C	4.8608	4.9392	4.8265	4.9735	0.196	0.343																
R3114x501A/C	4.9600	5.0400	4.9250	5.0750	0.200	0.350																

<sup>\*</sup>Note1) V<sub>DD</sub> value when output voltage is equal or less than 0.1V. In the case of Nch Open Drain output type, the output pin is pulled up to 5.0V through 470kΩ resistor.

Curr	er Output ent1	Curr	Nch Driver Output Current2 IOUT2 [mA]		Pch Driver Output Current		Oriver Current	Detector Threshold Temperature Coefficient ∆-VDET/∆Topt [ppm/°C]	Output Tin	те
Cond.	Min.	Cond.	Min.	Cond.	Min.	Cond.	Max.	Тур.	Cond.	Typ.
Cond.	V <sub>DD</sub> 0.6' V <sub>DS</sub>	V <sub>DD</sub> = 0.6V V <sub>DS</sub> = 0.5V	0.020	Cond.	Willi.	Cond.	wax.	Typ.	Cond.	Typ.
		V <sub>DD</sub> = 1.0V V <sub>DS</sub> = 0.5V	0.400							
V <sub>DD</sub> = 0.55V V <sub>DS</sub> = 0.05V	7	V <sub>DD</sub> = 1.5V V <sub>DS</sub> = 0.5V	1.000	V <sub>DD</sub> = 4.5V V <sub>DS</sub> = -2.1V	0.650	V <sub>DD</sub> = 6.0V V <sub>DS</sub> = 7.0V	80	±30	V <sub>DD</sub> = 0.55V ↓ -V <sub>DET</sub> +2.0V *Note2	40
		V <sub>DD</sub> = 3.0V V <sub>DS</sub> = 0.5V	2.400	Von=		7.00			Voo-	
				V <sub>DD</sub> = 6.0V V <sub>DS</sub> = -2.1V	0.900				V <sub>DD</sub> = 0.55V ↓ 6.0V *Note2	

#### \*Note2) 1. In the case of CMOS output type:

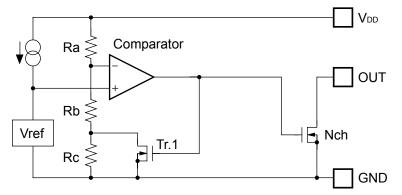
When the voltage is forced from 0.55V to  $(-V_{DET})+2.0V$  or a 6.0V pulse voltage is added to  $V_{DD}$ , time interval that the output voltage reaches  $((-V_{DET})+2.0V)/2$  or a 3.0V.

2. In the case of Nch Open Drain output type:

The output pin is pulled up to 5.0V through  $470k\Omega$ , and when the voltage is forced from 0.55V to (-VDET)+2.0V or a 6.0V pulse voltage is added to VDD, time interval that the output voltage reaches 2.5V.

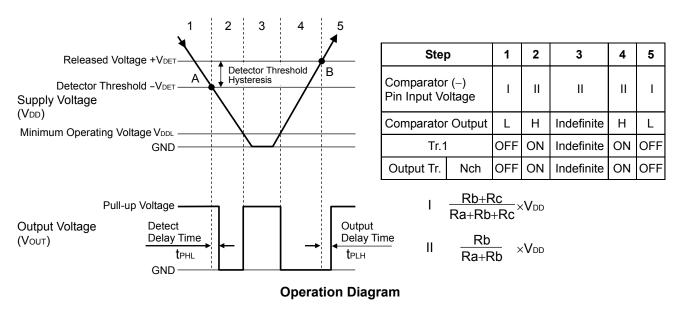
#### **OPERATION**

#### • Operation of R3114xxx1A



OUT pin should be pulled-up to V<sub>DD</sub> or an external voltage level.

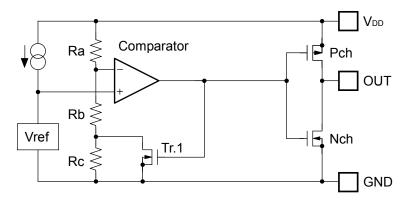
#### Block Diagram (R3114xxx1A)



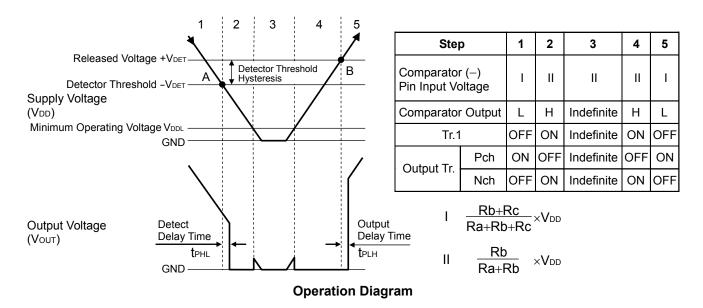
#### Explanation of operation

- Step 1. The output voltage is equal to the pull-up voltage.
- Step 2. At Point "A", Vref  $\geq V_{DD\times}(Rb+Rc)/(Ra+Rb+Rc)$  is true, as a result, the output of comparator is reversed from "L" to "H", therefore the output voltage becomes the GND level. The voltage level of Point A means a detector threshold voltage (-VDET).
- Step 3. When the supply voltage is lower than the minimum operating voltage, the operation of the output transistor becomes indefinite. The output voltage is equal to the pull-up voltage.
- Step 4. The output voltage is equal to the GND level.
- Step 5. At Point "B", Vref ≤ V<sub>DD</sub>×Rb/(Ra+Rb) is true, as a result, the output of comparator is reversed from "H" to "L", then the output voltage is equal to the pull-up voltage. The voltage level of Point B means a released voltage (+V<sub>DET</sub>).
- \*) The difference between a released voltage and a detector threshold voltage is a detector threshold hysteresis.

#### Operation of R3114xxx1C



Block Diagram (R3114xxx1C)

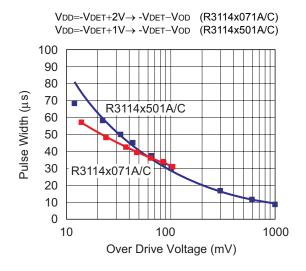


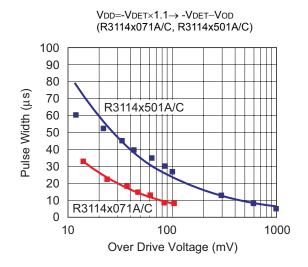
#### Explanation of operation

- Step 1. The output voltage is equal to the supply voltage ( $V_{\text{DD}}$ ).
- Step 2. At Point "A", Vref ≥ VDDX(Rb+Rc)/(Ra+Rb+Rc) is true, as a result, the output of comparator is reversed from "L" to "H", therefore the output voltage becomes the GND level. The voltage level of Point A means a detector threshold voltage (-VDET).
- Step 3. When the supply voltage is lower than the minimum operating voltage, the operation of the output transistor becomes indefinite.
- Step 4. The output voltage is equal to the GND level.
- Step 5. At Point "B", Vref ≤ V<sub>DD</sub>×Rb/(Ra+Rb) is true, as a result, the output of comparator is reversed from "H" to "L", then the output voltage is equal to the supply voltage (V<sub>DD</sub>). The voltage level of Point B means a released voltage (+V<sub>DET</sub>).
- \*) The difference between a released voltage and a detector threshold voltage is a detector threshold hysteresis.

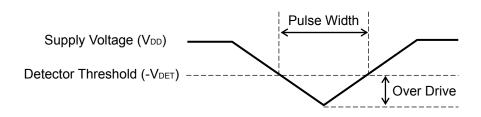
### Detector Operation vs. glitch input voltage to the VDD pin

When the R3114x is at released, if the pulse voltage which the detector threshold or lower voltage, the graph below means that the relation between pulse width and the amplitude of the swing to keep the released state for the R3114x.





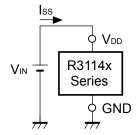
\*Vod: Over Drive Voltage



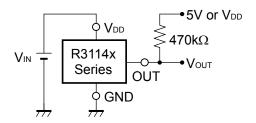
**VDD Input Waveform** 

This graph shows the maximum pulse conditions to keep the released voltage. If the pulse with larger amplitude or wider width than the graph above, is input to  $V_{DD}$  pin, the reset signal may be output.

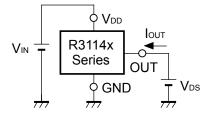
### **TEST CIRCUITS**



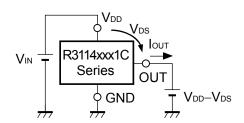
**Supply Current Test Circuit** 



**Detector Threshold Test Circuit** (Pull-up circuit is not necessary for CMOS Output type.)

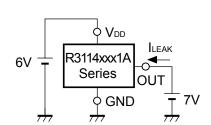


**Nch Driver Output Current Test Circuit** 

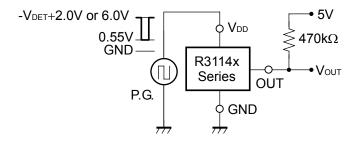


Pch Driver Output Current Test Circuit

\*Apply to CMOS Output type only



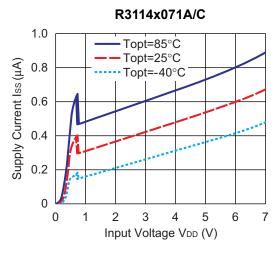
Nch Driver Leakage Current Test Circuit
\*Apply to Nch Driver Output type only

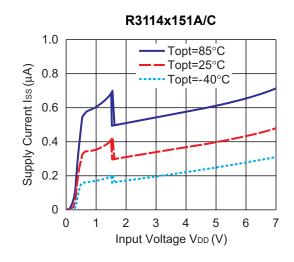


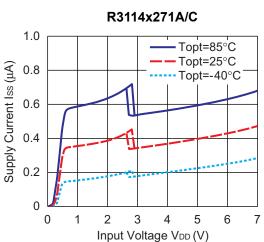
Output Delay Time Test Circuit (Pull-up circuit is not necessary for CMOS Output type.)

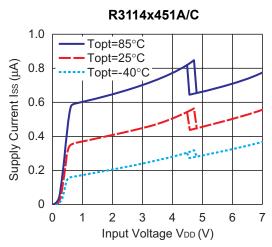
### **TYPICAL CHARACTERISTICS**

#### 1) Supply Current vs. Input Voltage

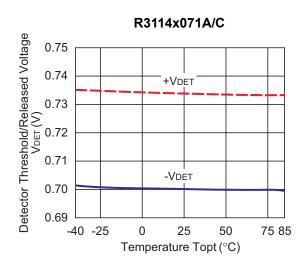


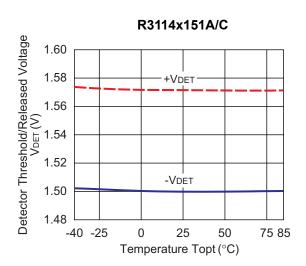




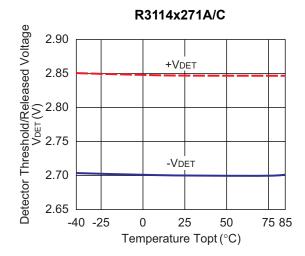


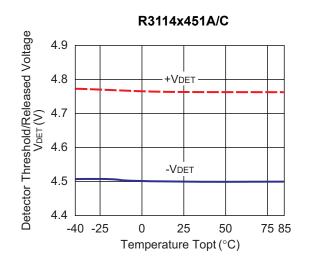
#### 2) Detector Threshold vs. Temperature



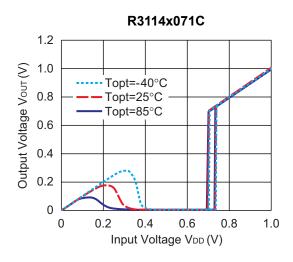


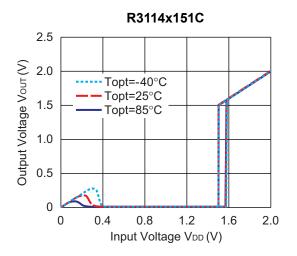
#### R3114x

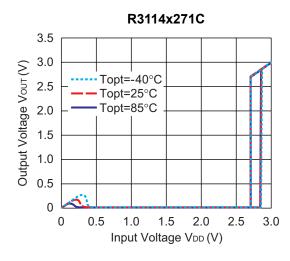


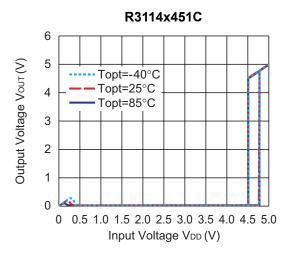


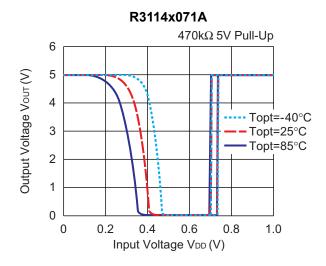
#### 3) Output Voltage vs. Input Voltage

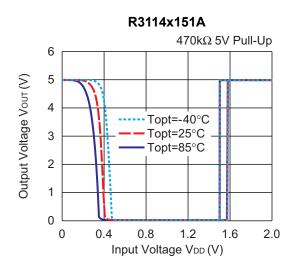


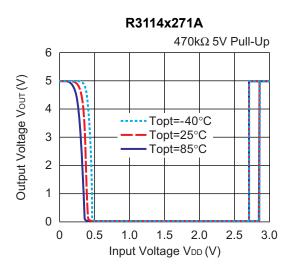


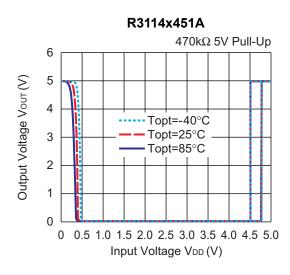




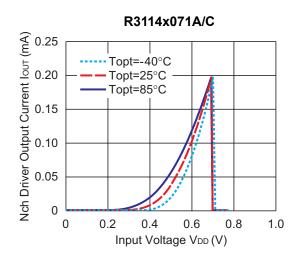


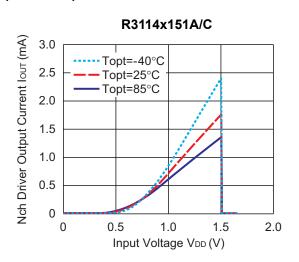




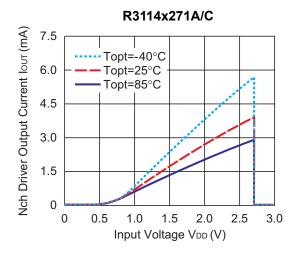


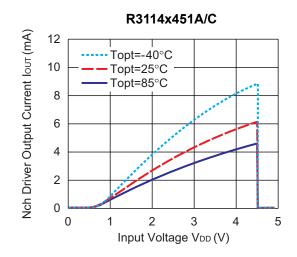
#### 4) Nch Driver Output Current vs. Input Voltage (VDS=0.5V)



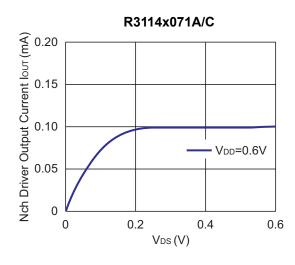


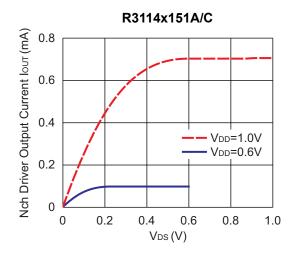
### R3114x

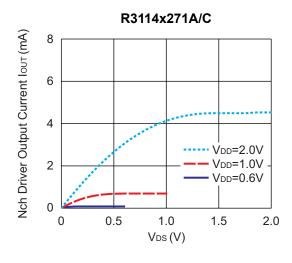


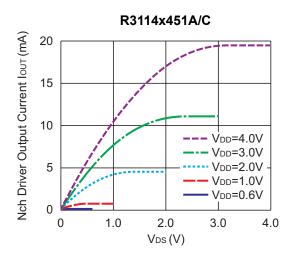


### 5) Nch Driver Output Current vs. VDS

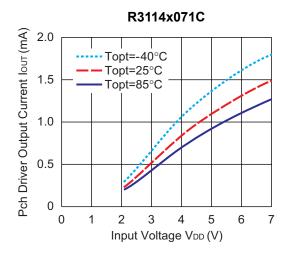


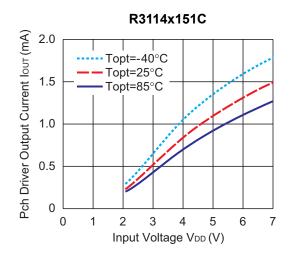


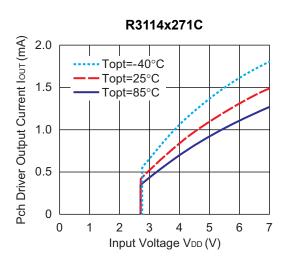


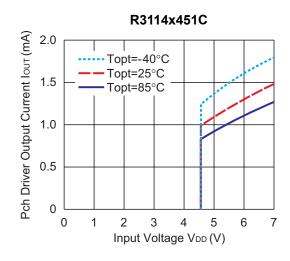


### 6) Pch Driver Output Current vs. Input Voltage (VDS=-2.1V)

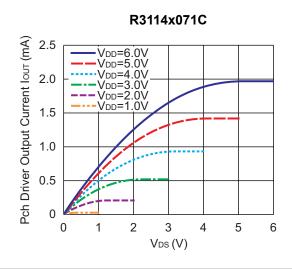


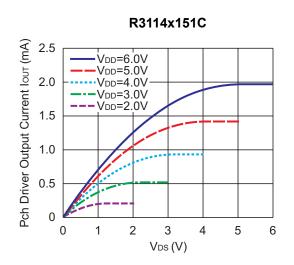




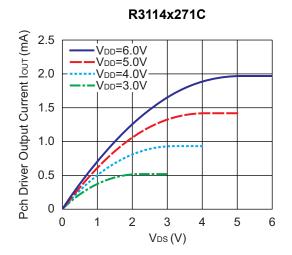


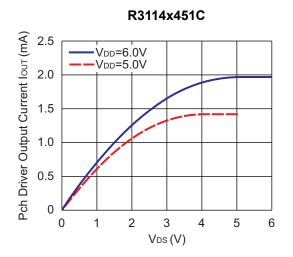
#### 7) Pch Driver Output Current vs. VDS



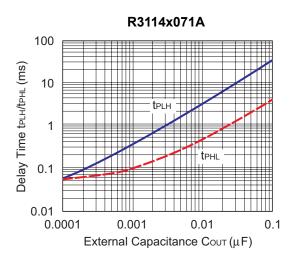


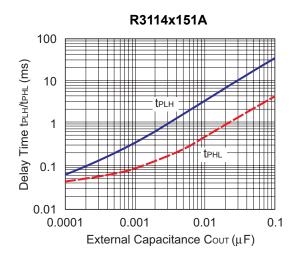
### R3114x

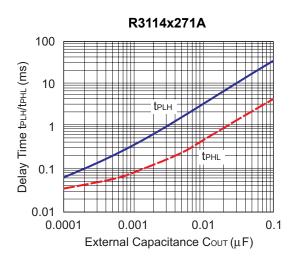


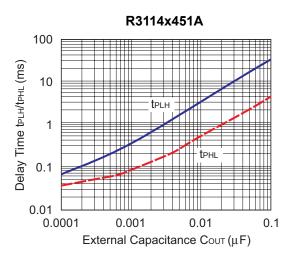


### 8) Output Delay Time vs. External Capacitance





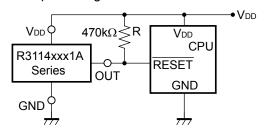




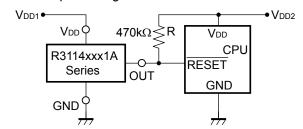
#### TYPICAL APPLICATION

• R3114xxx1A CPU Reset Circuit 1 (Nch Open Drain Output)

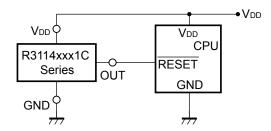
Case1. Input Voltage to R3114xxx1A is equal to Input Voltage to CPU



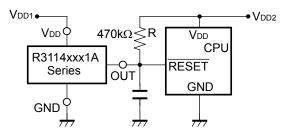
Case2. Input Voltage to R3114xxx1A is unequal to Input Voltage to CPU



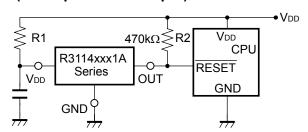
• R3114xxx1C CPU Reset Circuit (CMOS Output)



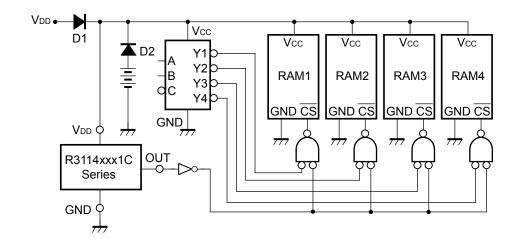
 R3114xxx1A Output Delay Time Circuit 1 (Nch Open Drain Output)



 R3114xxx1A Output Delay Time Circuit 2 (Nch Open Drain Output)

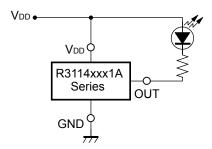


Memory Back-up Circuit

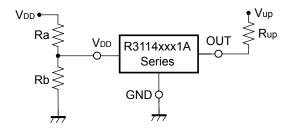


#### R3114x

 Voltage level Indicator Circuit (lighted when the power runs out) (Nch Open Drain Output)



 Detector Threshold Adjustable Circuit 1 (Nch Open Drain Output)

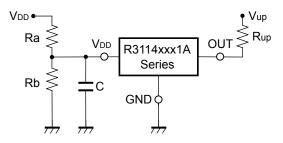


Adjustable Detector Threshold=(-VDET)×(Ra+Rb)/Rb

Hysteresis Voltage=(VHYS)×(Ra+Rb)/Rb

- \*1) To prevent oscillation, set  $Ra \le 1k\Omega$ ,  $Rb \le 100\Omega$ .
- \*2) If the value of Ra is set excessively large, voltage drop may occur caused by the supply current of IC itself, and detector threshold and hysteresis voltage may vary
- \*3) If Vup and VDD are connected, the voltage dropdown caused by Rup, may cause difference in the hysteresis voltage.

 Detector Threshold Adjustable Circuit 2 (Nch Open Drain Output)

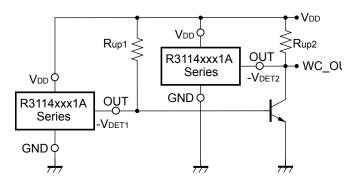


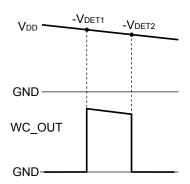
Adjustable Detector Threshold=(-VDET)×(Ra+Rb)/Rb

Hysteresis Voltage=(VHYS)×(Ra+Rb)/Rb

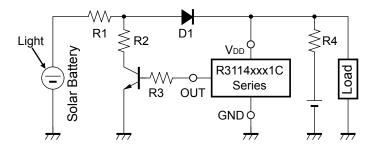
- \*1) To prevent oscillation, set Ra  $\leq 100 k\Omega,\, C \geq ~\leq 0.01 \mu F.$
- \*2) If the value of Ra is set excessively large, voltage drop may occur caused by the supply current of IC itself, and detector threshold and hysteresis voltage may vary.
- \*3) If Vup and Vdd are connected, the voltage dropdown caused by Rup, may cause difference in the hysteresis voltage.
- \*4) If the value of Ra, Rb and C are set excessively large, the delay of the start-up may become too long.

### Window Comparator Circuit (Nch Open Drain Output)





### • Over-charge Preventing Circuit

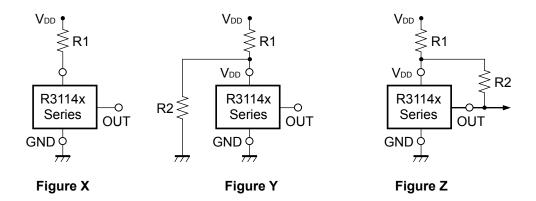


#### **TECHNICAL NOTES**

When R3114xxx1A/C is used in Figure X, if the value of R1 is set excessively large, the dropdown voltage caused by the consumption current of IC itself, may vary the detector threshold and the release voltage. Also, if the value of R1 is set excessively large, there may be delay in start-up and may cause oscillation generated by cross conduction current.

When R3114xxx1A/C is used in Figure Y, if the value of R1 is set excessively large, the dropdown voltage caused by the consumption current of IC itself, may vary the detecor threshold and the released voltage. Also, if the value of R1 and R2 is set excessively large, there may be delay in start-up and may cause oscillation generated by cross conduction current.

When R3114xxx1A/C is used in Figure Z, if the value of R1 is set excessively large, the dropdown voltage caused by the consumption current of IC itself may vary the detector threshold and the release voltage. Also, if the value of R1 is set excessively large, there may be delay in start-up and may cause oscillation generated by cross conduction current. Furthermore, if the value of R1 is set large and the value of R2 is set small, released voltage level may shift and the minimum operating voltage may differ. If the value of R2 is set excessively small from R1, release may not occur and may cause oscillation.





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